



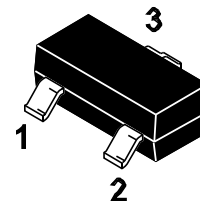
PJM07P20SA

P-Channel Enhancement Mode Power MOSFET

Features

- Low gate charge
- High density cell design for ultra low $R_{DS(on)}$
- $V_{DS} = -20V, I_D = -7A$
 $R_{DS(on)} < 28m\Omega @ V_{GS} = -10V$

SOT-23



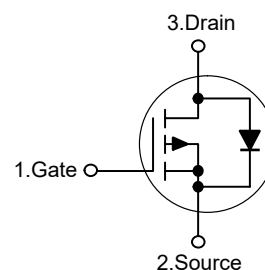
1. Gate 2. Source 3. Drain

Marking Code: MOA

Applications

- Load Switch and in PWM Applications

Schematic Diagram



Absolute Maximum Ratings

Ratings at 25°C ambient temperature unless otherwise specified.

| Parameter | Symbol | Value | Unit |
|---------------------------------------|-----------|-------------|------|
| Drain-Source Voltage | $-V_{DS}$ | 20 | V |
| Gate-Source Voltage | V_{GS} | ± 12 | V |
| Drain Current-Continuous | $-I_D$ | 7 | A |
| Drain Current-Pulsed ^{Note1} | I_{DM} | 28 | A |
| Maximum Power Dissipation | P_D | 1.2 | W |
| Junction Temperature | T_J | 150 | °C |
| Storage Temperature Range | T_{STG} | -55 to +150 | °C |

Thermal Characteristics

| | | | |
|---|-----------------|-----|------|
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 104 | °C/W |
|---|-----------------|-----|------|



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Electrical Characteristics

(Ta=25°C unless otherwise specified)

| Parameter | Symbol | Test Condition | Min. | Typ. | Max. | Unit |
|---|----------------|---|------|------|-----------|------------|
| Static Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | $-V_{(BR)DSS}$ | $V_{GS}=0V, I_D=-250\mu A$ | 20 | -- | -- | V |
| Zero Gate Voltage Drain Current | $-I_{DSS}$ | $V_{DS}=-20V, V_{GS}=0V$ | -- | -- | 1 | μA |
| Gate-Body Leakage Current | I_{GSS} | $V_{GS}=\pm 12V, V_{DS}=0V$ | -- | -- | ± 100 | nA |
| Gate Threshold Voltage ^{Note2} | $-V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=-250\mu A$ | 0.4 | 0.7 | 1.0 | V |
| Drain-Source On-Resistance ^{Note2} | $R_{DS(on)}$ | $V_{GS}=-10V, I_D=-4.1A$ | -- | 17 | 28 | m Ω |
| | | $V_{GS}=-4.5V, I_D=-3A$ | -- | 20 | 35 | m Ω |
| Forward Transconductance ^{Note2} | g_{FS} | $V_{DS}=-5V, I_D=-2A$ | -- | 10 | -- | S |
| Dynamic Characteristics | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS}=-10V, V_{GS}=0V, f=1MHz$ | -- | 2000 | -- | pF |
| Output Capacitance | C_{oss} | | -- | 242 | -- | pF |
| Reverse Transfer Capacitance | C_{rss} | | -- | 231 | -- | pF |
| Switching Characteristics | | | | | | |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DD}=-10V, I_D=-7A$ $V_{GS}=-4.5V, R_{GEN}=2.5\Omega$ | -- | 10 | -- | nS |
| Turn-on Rise Time | t_r | | -- | 31 | -- | nS |
| Turn-off Delay Time | $t_{d(off)}$ | | -- | 28 | -- | nS |
| Turn-off Fall Time | t_f | | -- | 8 | -- | nS |
| Total Gate Charge | Q_g | $V_{DS}=-10V,$ $V_{GS}=-4.5V, I_D=-3A$ | -- | 15.3 | -- | nC |
| Gate-Source Charge | Q_{gs} | | -- | 2.2 | -- | nC |
| Gate-Drain Charge | Q_{gd} | | -- | 4.4 | -- | nC |
| Source-Drain Diode Characteristics | | | | | | |
| Diode Forward Voltage | $-V_{SD}$ | $V_{GS}=0V, I_S=-7A$ | -- | -- | 1.2 | V |
| Diode Forward Current | $-I_S$ | | -- | -- | 7 | A |

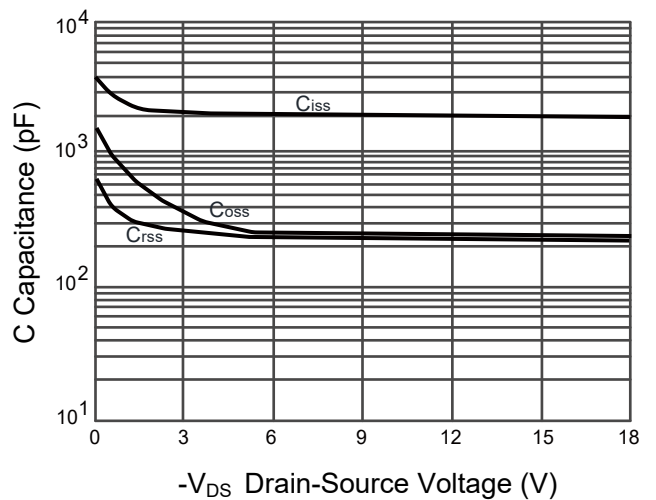
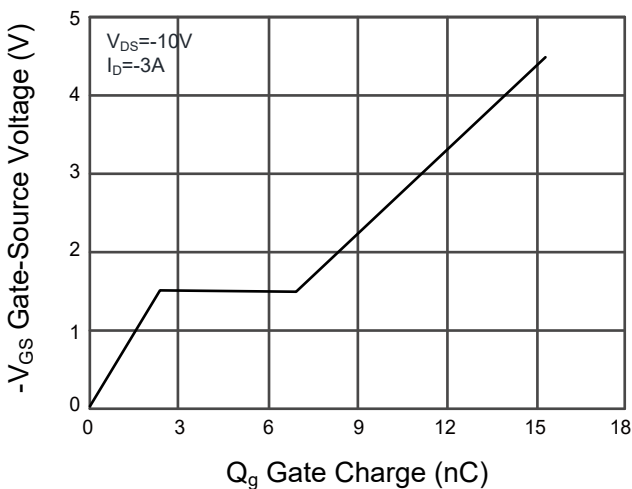
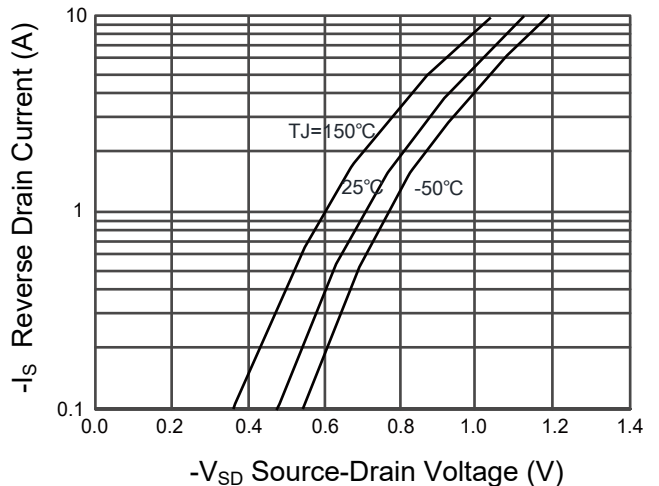
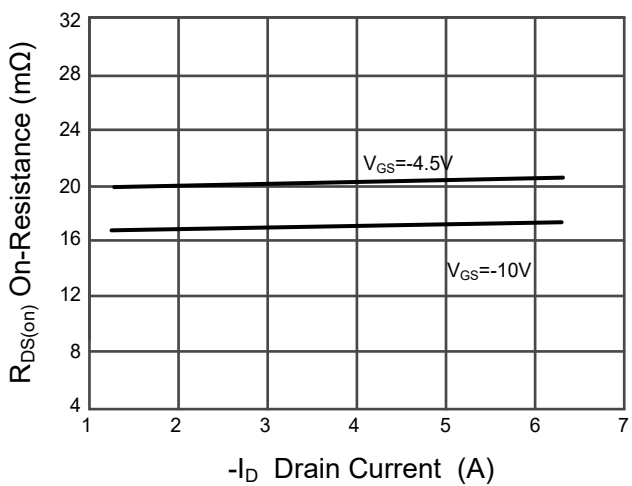
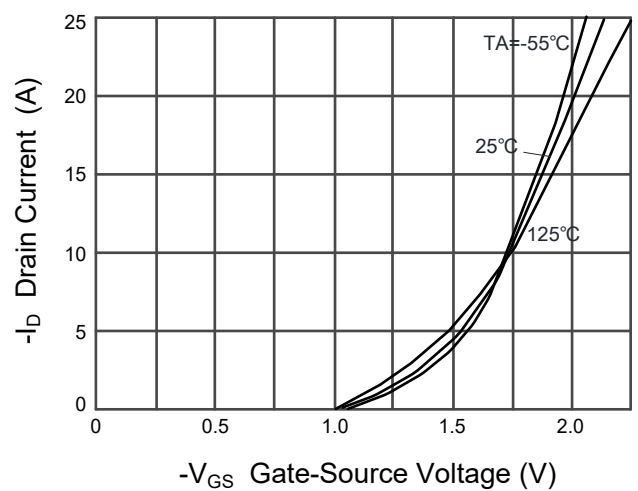
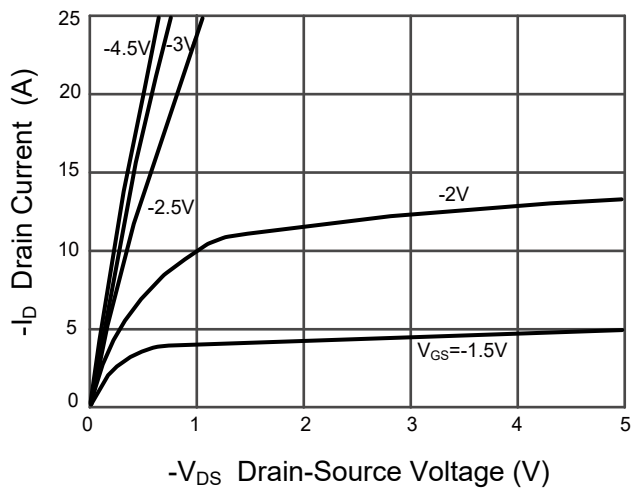
Note: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. Pulse Test: Pulse width $\leq 300\mu s$, duty cycles $\leq 2\%$



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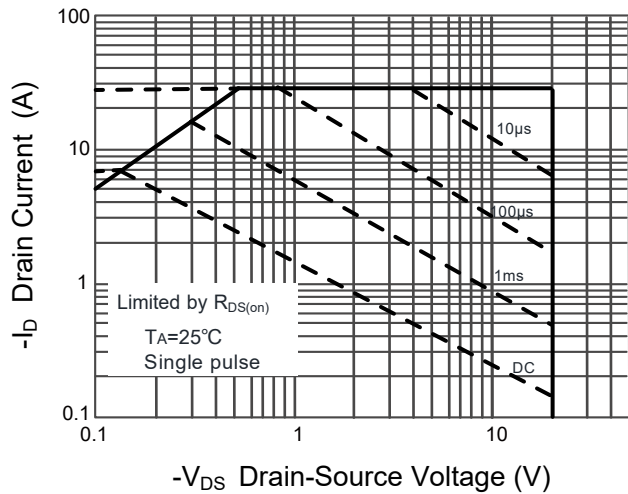
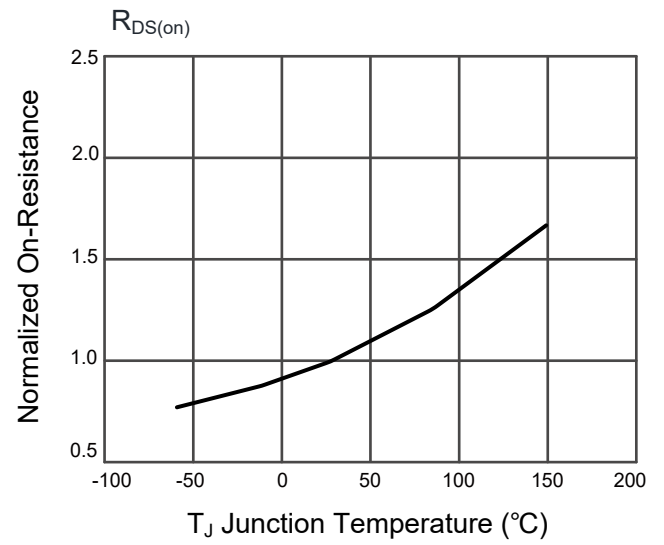
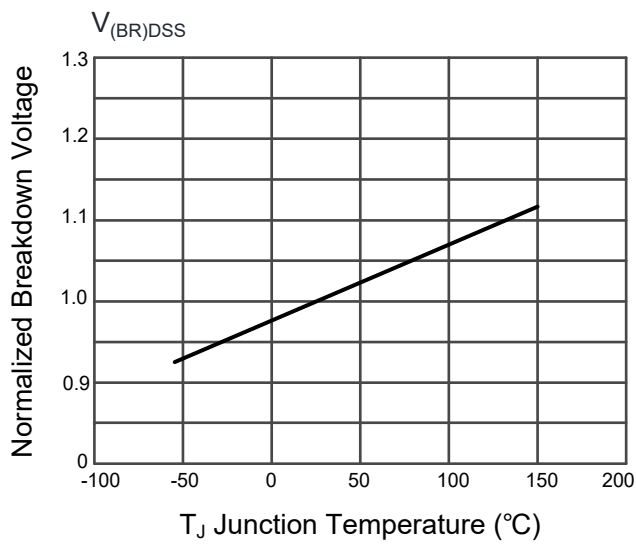
Typical Characteristic Curves





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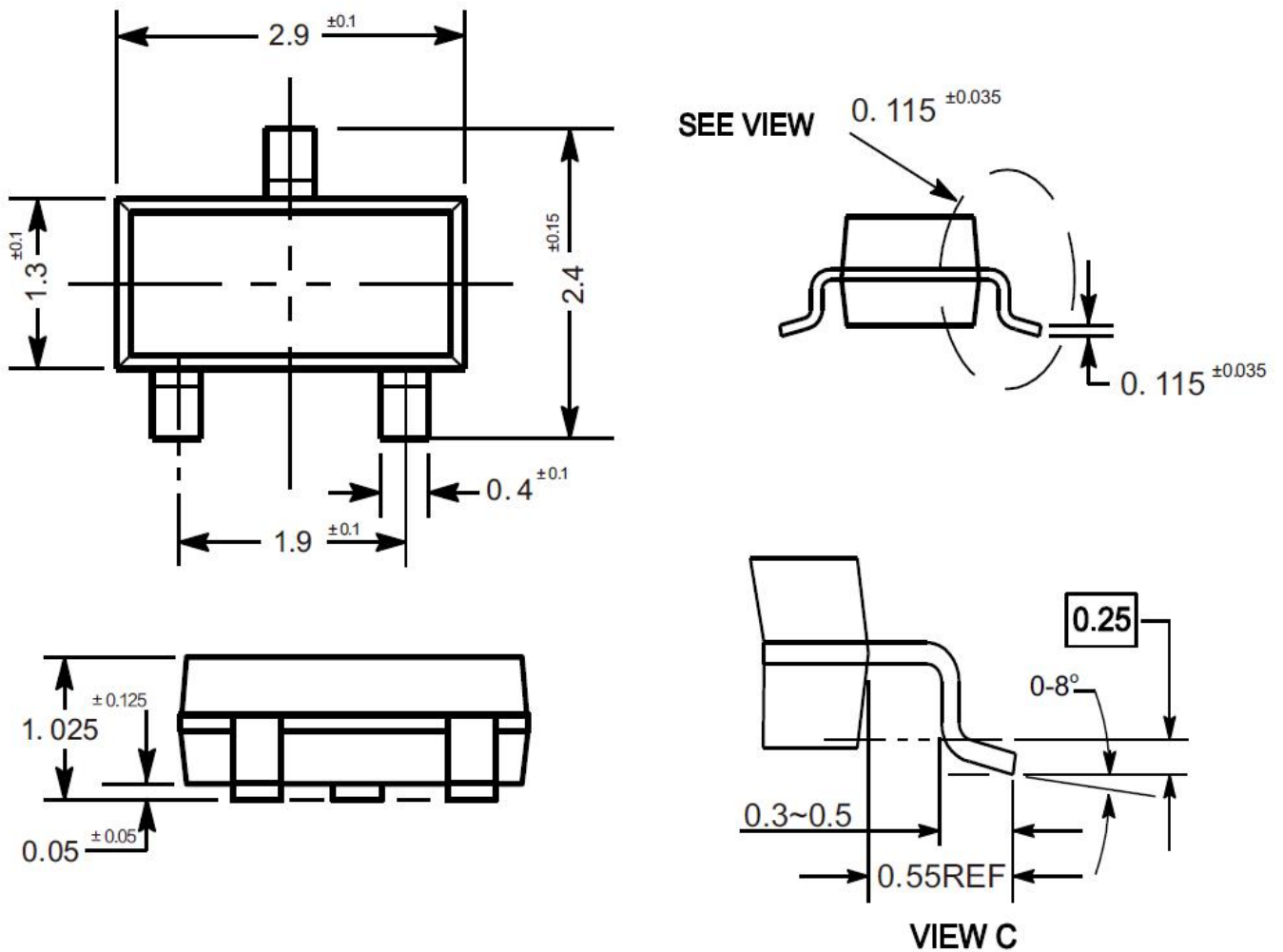
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Package Outline

SOT-23

Dimensions in mm



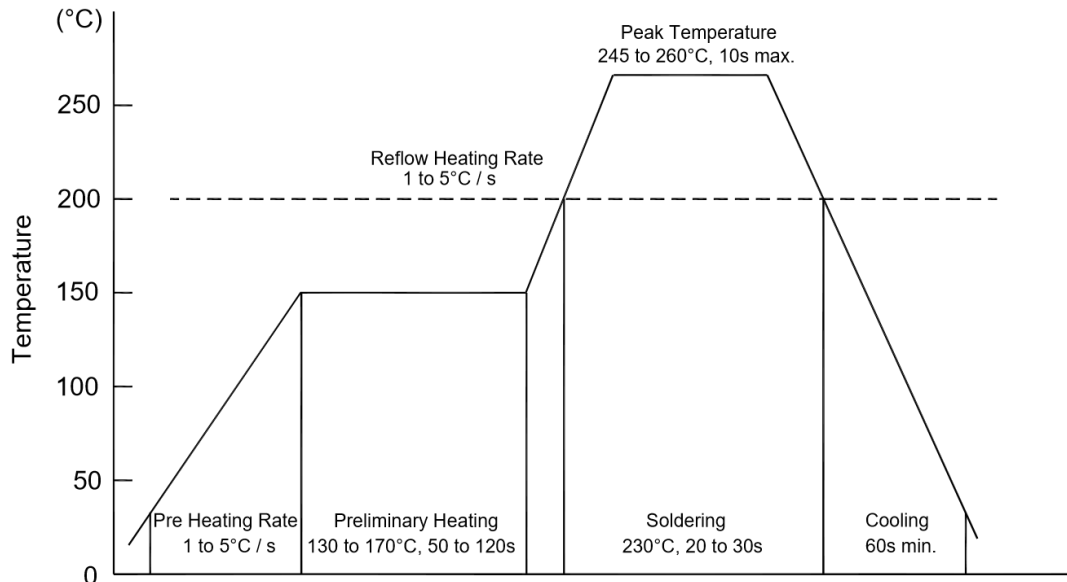
Ordering Information

| Device | Package | Shipping |
|------------|---------|-----------------------|
| PJM07P20SA | SOT-23 | 3,000PCS/Reel&7inches |



Conditions of Soldering and Storage

◆ Recommended condition of reflow soldering



Recommended peak temperature is over 245 °C. If peak temperature is below 245 °C, you may adjust the following parameters:

- Time length of peak temperature (longer)
- Time length of soldering (longer)
- Thickness of solder paste (thicker)

◆ Conditions of hand soldering

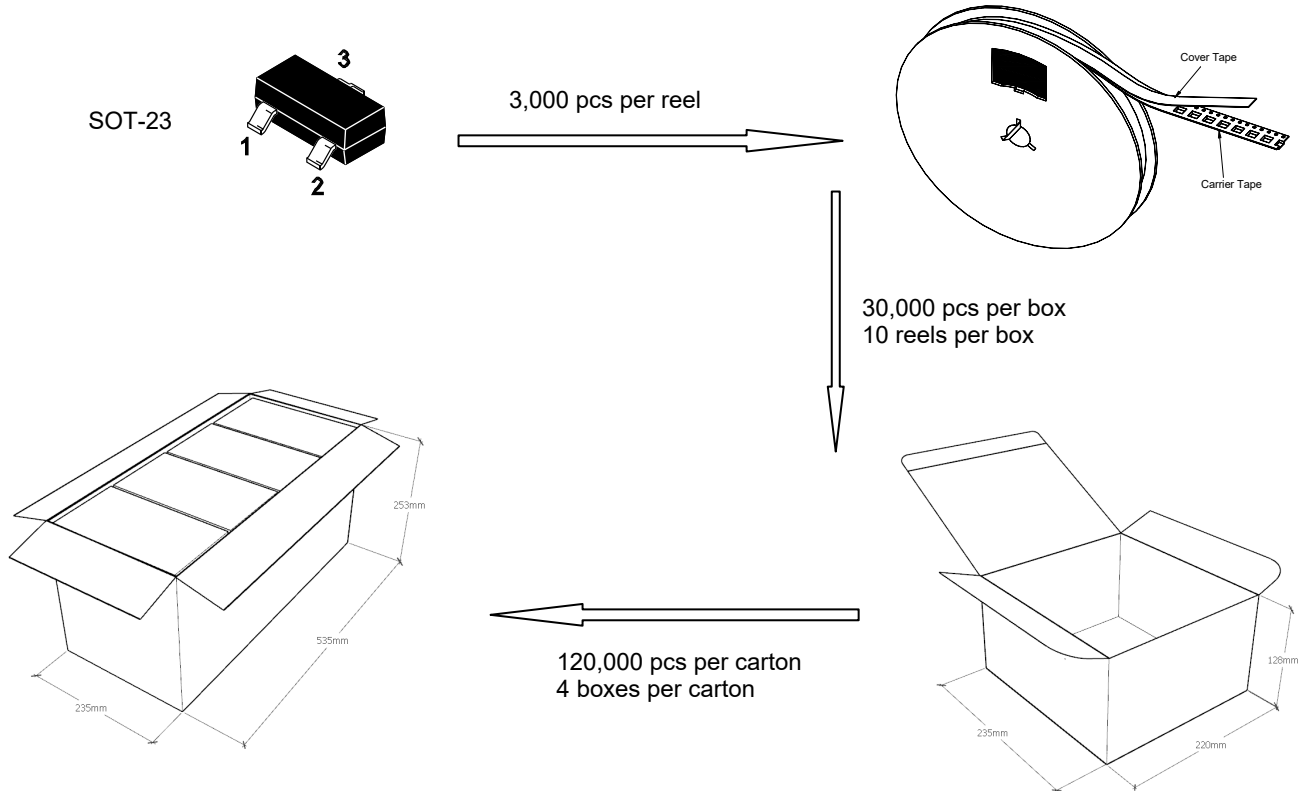
- Temperature: 370 °C
- Time: 3s max.
- Times: one time

◆ Storage conditions

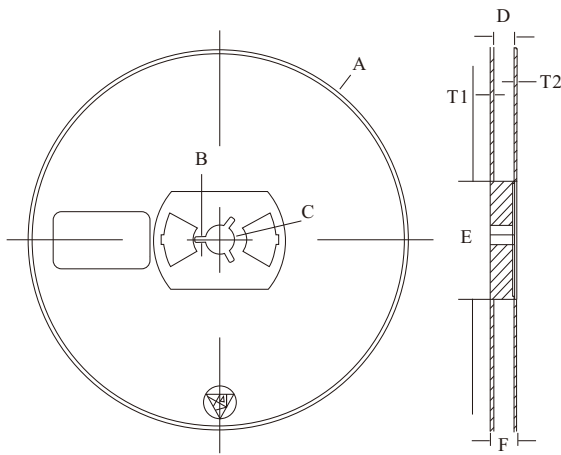
- **Temperature**
5 to 40 °C
- **Humidity**
30 to 80% RH
- **Recommended period**
One year after manufacturing

Package Specifications

- The method of packaging

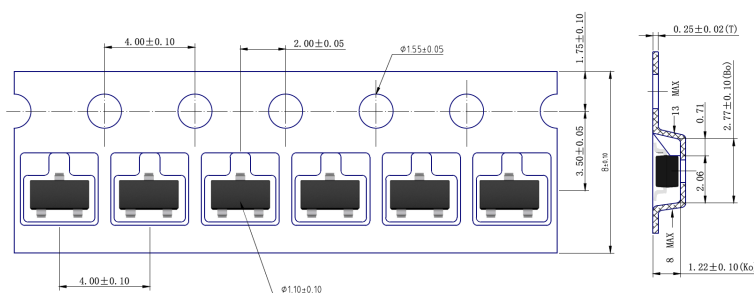


◆ Embossed tape and reel data



| Symbol | Value (unit: mm) |
|--------|------------------|
| A | Ø 177.8±1 |
| B | 2.7±0.2 |
| C | Ø 13.5±0.2 |
| E | Ø 54.5±0.2 |
| F | 12.3±0.3 |
| D | 9.6+2/-0.3 |
| T1 | 1.0±0.2 |
| T2 | 1.2±0.2 |

Reel (7")



单击下面可查看定价，库存，交付和生命周期等信息

[>>PJSEMI\(平晶微\)](#)